

SWITCHING REGULATOR APPLICATIONS

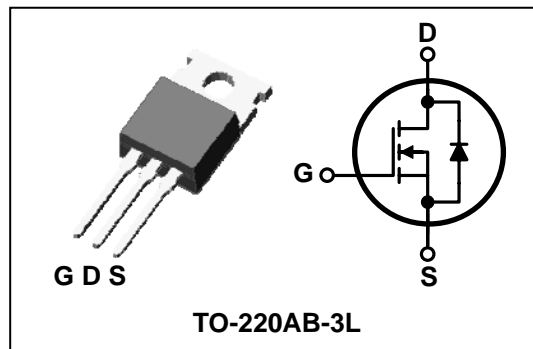
Features

- High Voltage: $BV_{DSS}=600V(\text{Min.})$
- Low C_{rSS} : $C_{rSS}=5.8pF(\text{Typ.})$
- Low gate charge : $Qg=13nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=2.5\Omega(\text{Max.})$

Ordering Information

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| SMK0460P | SMK0460 | TO-220AB-3L |

PIN Connection



Absolute maximum ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Rating | Unit |
|----------------------------------|-----------|-----------------------------|------------------|
| Drain-source voltage | V_{DSS} | 600 | V |
| Gate-source voltage | V_{GSS} | ± 30 | V |
| Drain current (DC) | I_D | ($T_c=25^\circ\text{C}$) | 4 |
| | | ($T_c=100^\circ\text{C}$) | 2.53 |
| Drain current (Pulsed) * | I_{DM} | 16 | A |
| Drain Power dissipation | P_D | 70 | W |
| Avalanche current (Single) ② | I_{AS} | 4 | A |
| Single pulsed avalanche energy ② | E_{AS} | 225 | mJ |
| Avalanche current (Repetitive) ① | I_{AR} | 4 | A |
| Repetitive avalanche energy ① | E_{AR} | 10 | mJ |
| Junction temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -55~150 | |

* Limited by maximum junction temperature

| Characteristic | Symbol | Typ. | Max | Unit |
|--------------------|------------------|------|------|---------------------------|
| Thermal resistance | Junction-case | - | 1.78 | $^\circ\text{C}/\text{W}$ |
| | Junction-ambient | - | 62.5 | |

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit | |
|--------------------------------|---------------------|-------------------------------------------------------------------|------|------|------|------|---|
| Drain-source breakdown voltage | BV _{DSS} | I _D =250μA, V _{GS} =0 | 600 | - | - | V | |
| Gate-threshold voltage | V _{GS(th)} | I _D =250μA, V _{DS} =V _{GS} | 2.0 | - | 4.0 | V | |
| Drain-source leakage current | I _{DSS} | V _{DS} =600V, V _{GS} =0V | - | - | 1 | μA | |
| Gate-source leakage | I _{GSS} | V _{DS} =0V, V _{GS} =±30V | - | - | ±100 | nA | |
| Drain-Source on-resistance ④ | R _{DS(ON)} | V _{GS} =10V, I _D =2.0A | - | 2.1 | 2.5 | Ω | |
| Forward transfer admittance ④ | g _{fs} | V _{DS} =10V, I _D =2.0A | - | 4.0 | - | S | |
| Input capacitance | C _{iss} | V _{GS} =0V, V _{DS} =25V, f=1MHz | - | 592 | 789 | pF | |
| Output capacitance | C _{oss} | | - | 54 | 72 | | |
| Reverse transfer capacitance | C _{rss} | | - | 5.8 | 7.7 | | |
| Turn-on delay time | t _{d(on)} | V _{DD} =300V, I _D =4A R _G =25Ω | - | 10 | - | ns | |
| Rise time | t _r | | - | 42 | - | | |
| Turn-off delay time | t _{d(off)} | | ③④ | - | 38 | | - |
| Fall time | t _f | | - | 46 | - | | |
| Total gate charge | Q _g | V _{DS} =480V, V _{GS} =10V I _D =4A | - | 13 | 17 | nC | |
| Gate-source charge | Q _{gs} | | - | 4 | - | | |
| Gate-drain charge | Q _{gd} | | ③④ | - | 3 | | - |

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------|-----------------|---------------------------------------------------|-----|-----|-----|------|
| Continuous source current | I _S | Integral reverse diode in the MOSFET | - | - | 4 | A |
| Source current (Pulsed) ① | I _{SM} | | - | - | 16 | |
| Forward voltage ④ | V _{SD} | V _{GS} =0V, I _S =4A | - | - | 1.4 | V |
| Reverse recovery time | t _{rr} | I _S =4A di _s /dt=100A/us | - | 300 | - | ns |
| Reverse recovery charge | Q _{rr} | | - | 2.2 | - | uC |

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=25.9mH, I_{AS}=4A, V_{DD}=50V, R_G=27Ω, Starting T_J = 25 °C
- ③ Pulse Test : Pulse Width < 300us, Duty cycle ≤ 2%
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

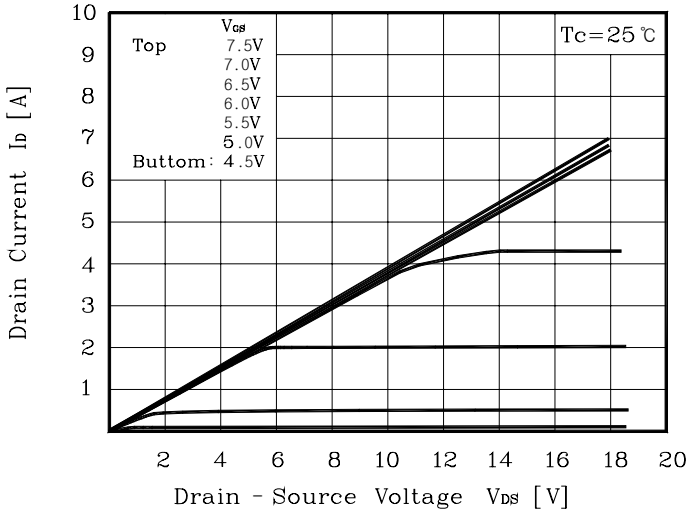


Fig. 2 $I_D - V_{GS}$

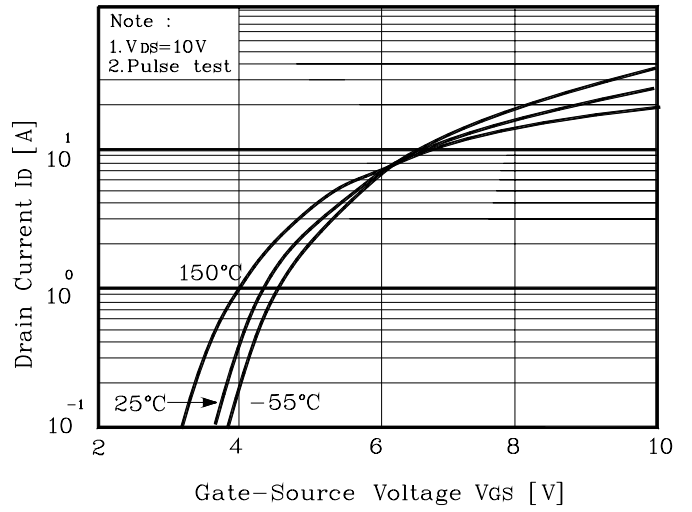


Fig. 3 $R_{DS(on)} - I_D$

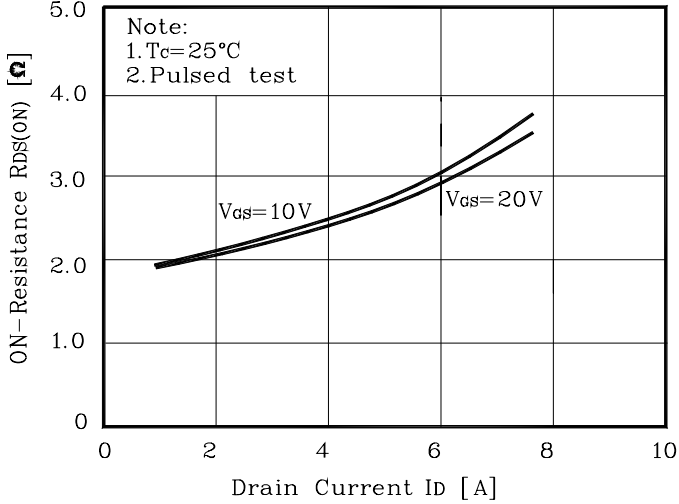


Fig. 4 $I_S - V_{SD}$

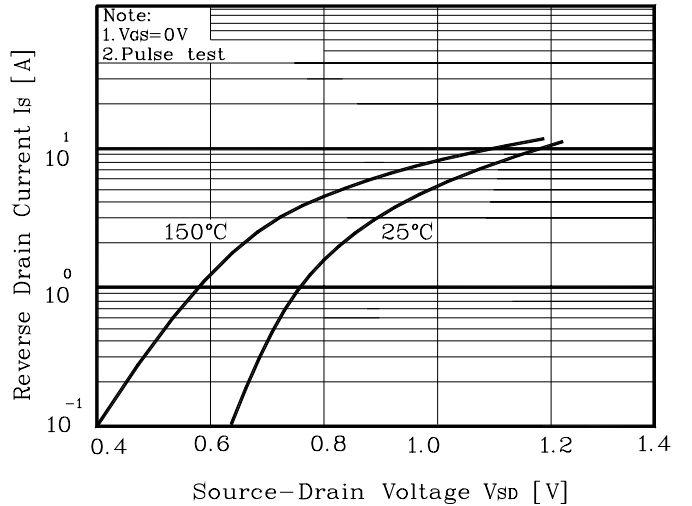


Fig. 5 Capacitance - V_{DS}

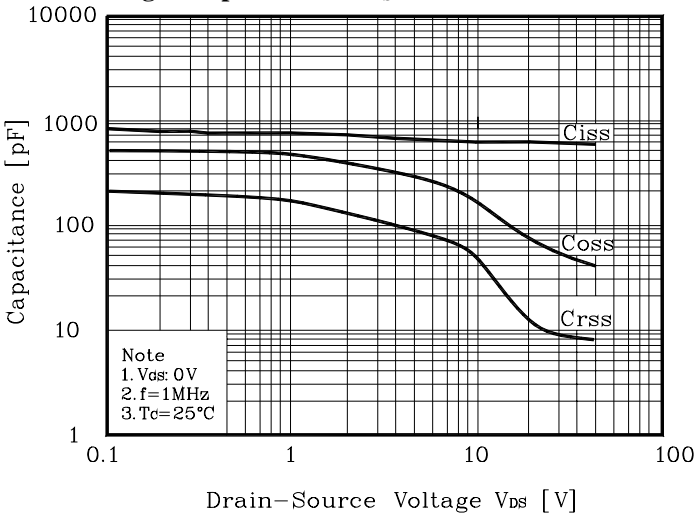
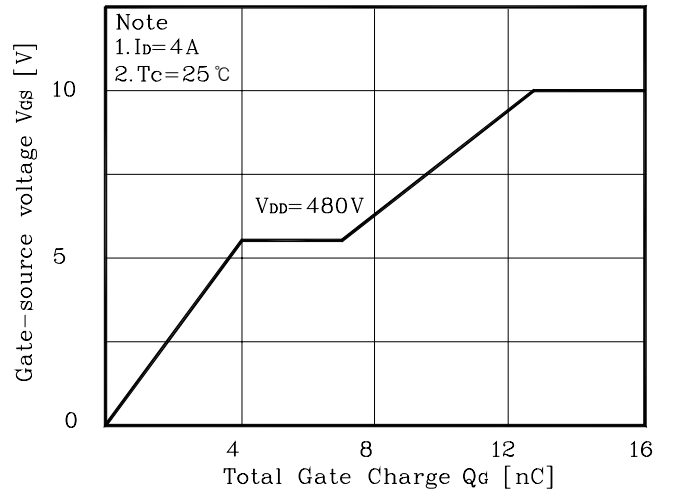


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristic Curves

Fig. 7 $V_{DSS} - T_J$

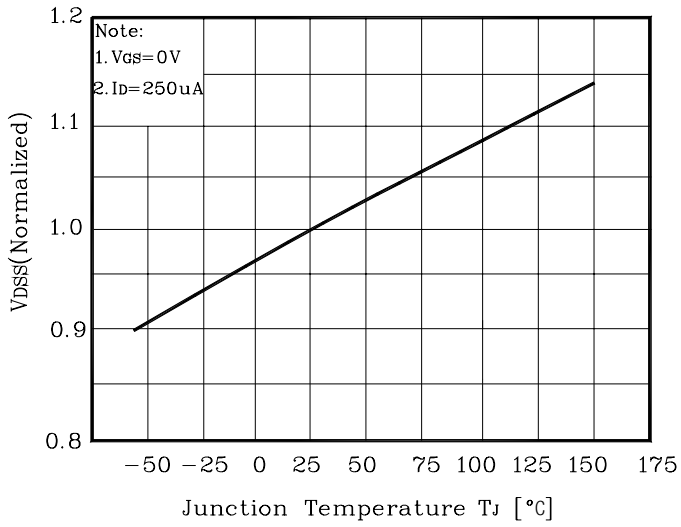


Fig. 8 $R_{DS(on)} - T_J$

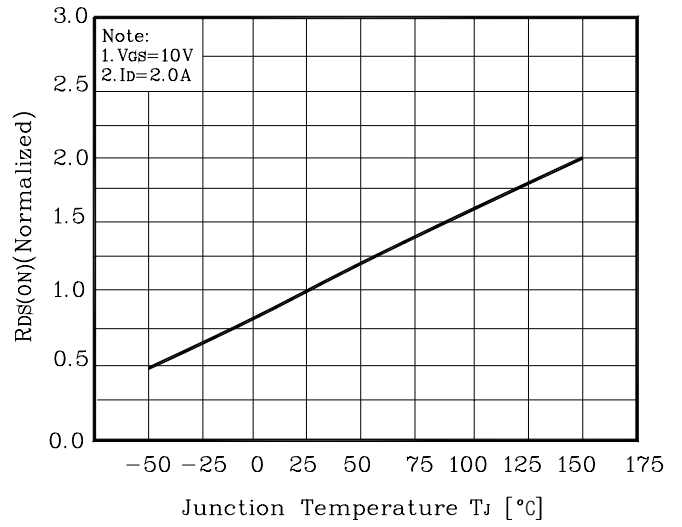


Fig. 9 $I_D - T_C$

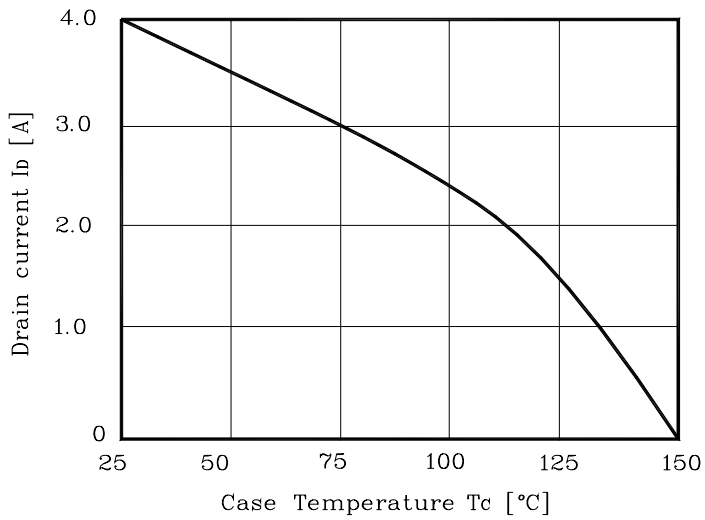


Fig. 10 Safe Operating Area

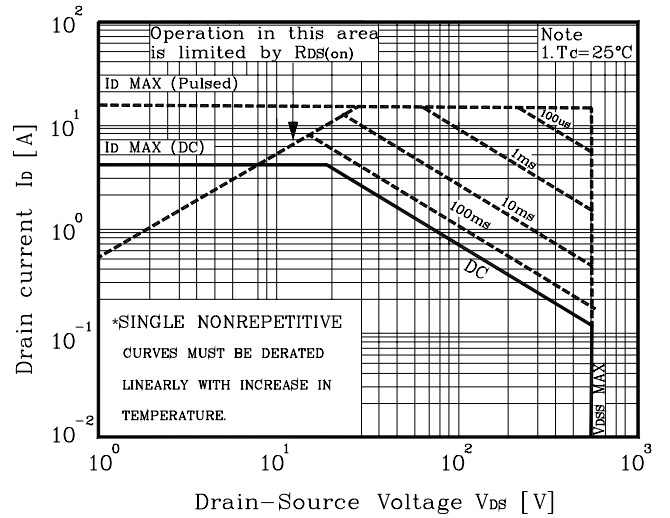


Fig. 11 Gate Charge Test Circuit & Waveform

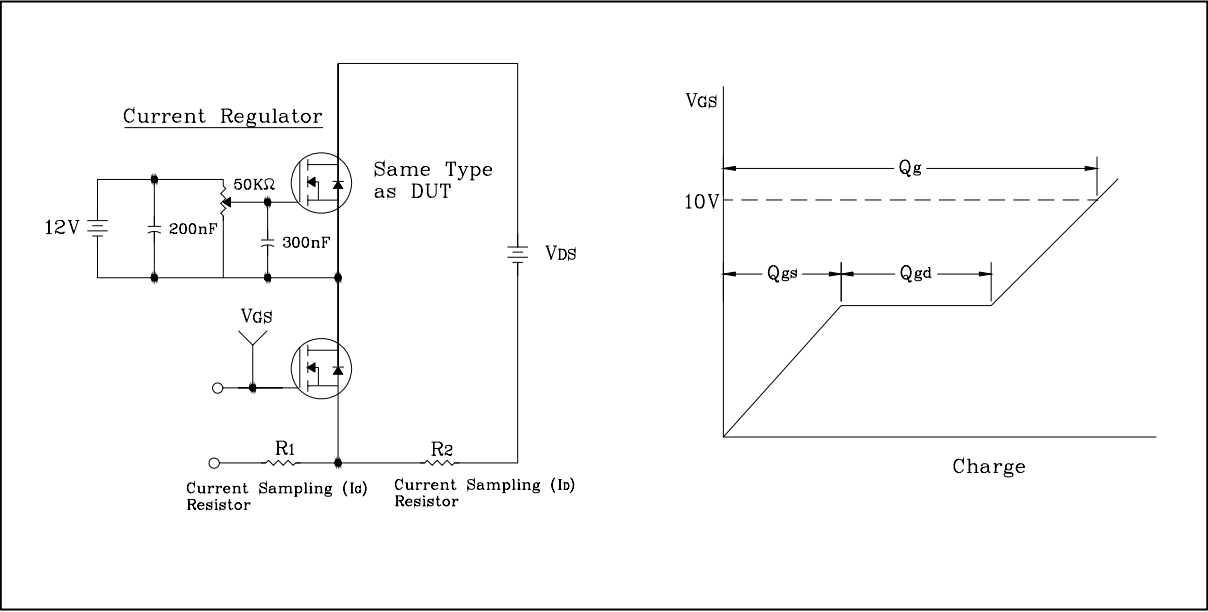


Fig. 12 Resistive Switching Test Circuit & Waveform

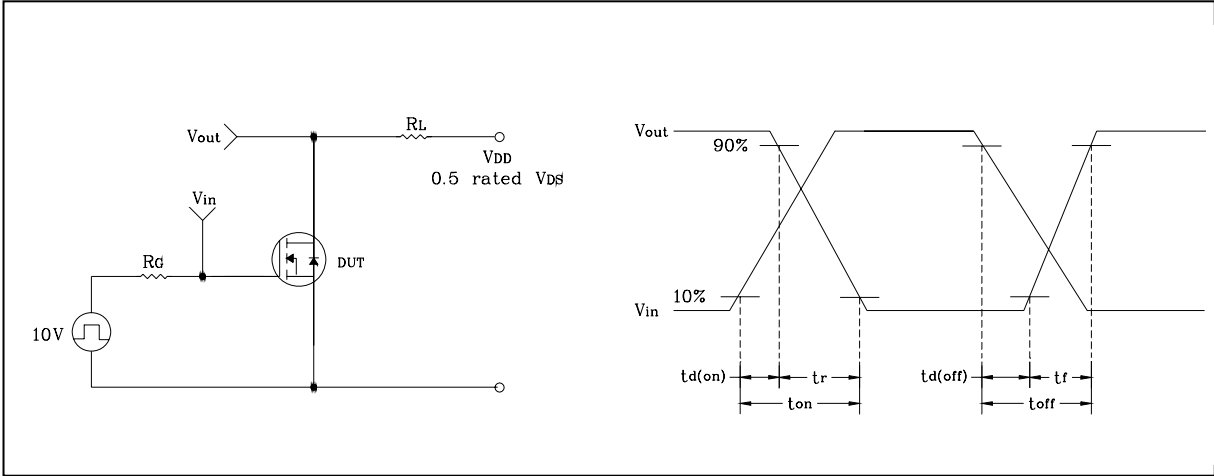


Fig. 13 E_{AS} Test Circuit & Waveform

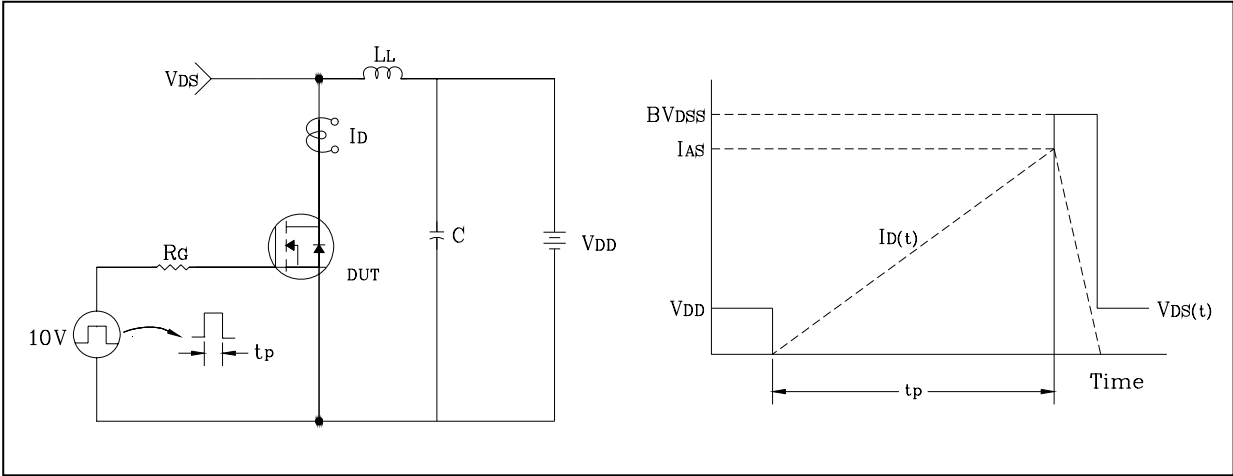
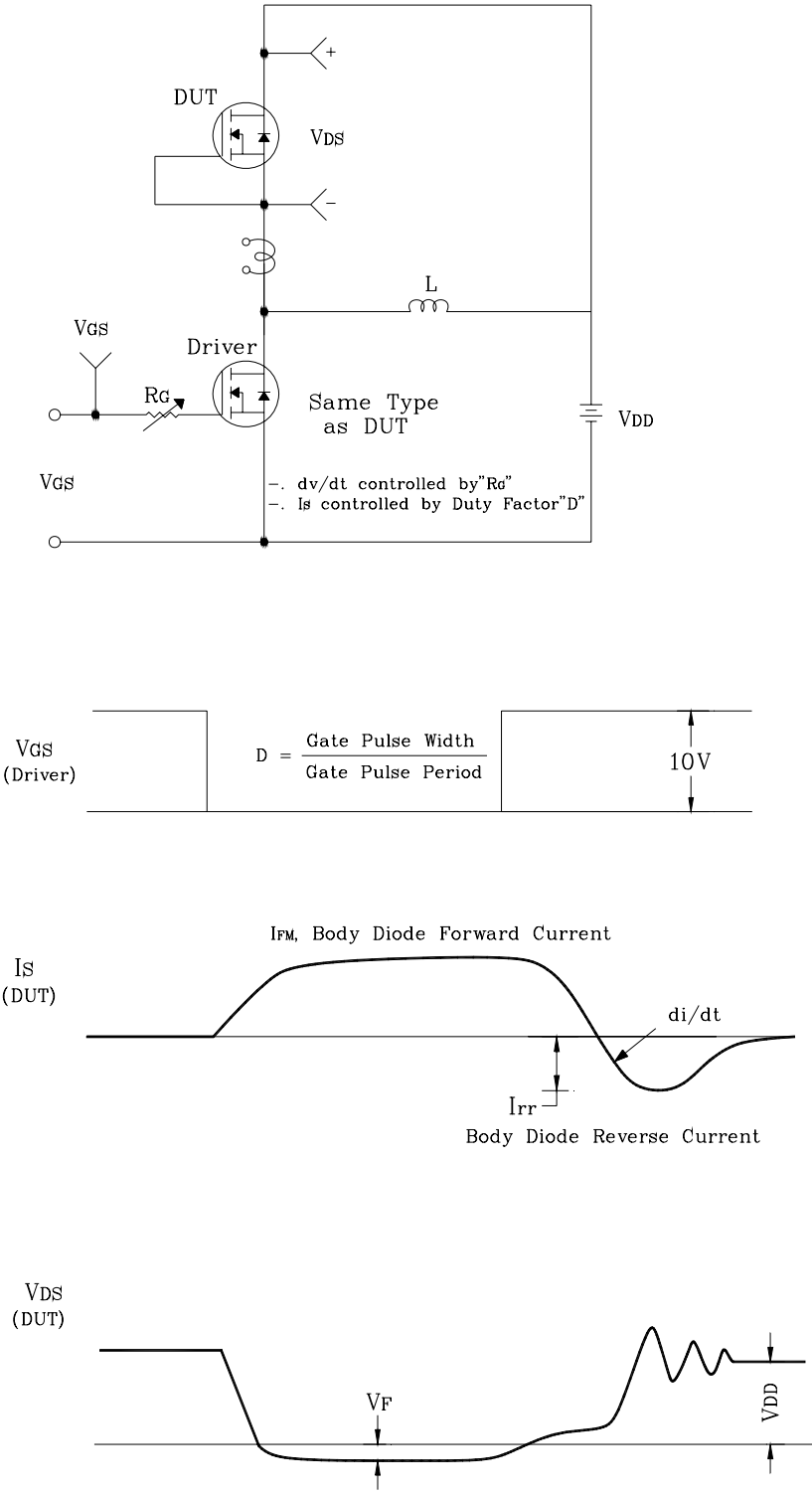
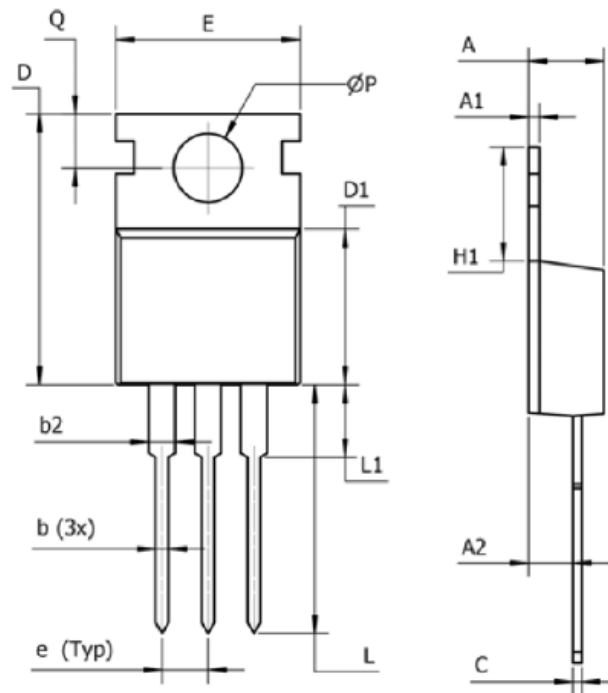


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Outline Dimension



| DIM | MM | INCHES |
|-----------------|-------------------------|---------------------------|
| D | 14.22-16.51 | 0.560-0.650 |
| $\varnothing P$ | $\varnothing 3.53-4.09$ | $\varnothing 0.139-0.161$ |
| H1 | 5.84-6.86 | 0.230-0.270 |
| b | 0.38-1.02 | 0.015-0.040 |
| b2 | 1.14-1.78 | 0.045-0.070 |
| D1 | 8.38-9.02 | 0.330-0.355 |
| e | 2.54 | 0.100 |
| E | 9.65-10.67 | 0.380-0.420 |
| L1 | 6.35(MAX) | 0.250(MAX) |
| A | 3.56-4.83 | 0.140-0.190 |
| A1 | 0.51-0.71 | 0.020-0.028 |
| L | 12.70-14.73 | 0.500-0.580 |
| A2 | 2.03-2.92 | 0.080-0.115 |
| Q | 2.54-3.43 | 0.100-0.135 |
| C | 0.36-0.61 | 0.014-0.024 |
| | | |

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